L Number	Hits	Search Text	DB	Time stamp
1	37	438/257,366,367,368,369,303.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/07 09:10
2	37	(channel adj region) 438/257,366,367,368,369,303.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/07 09:10
3	1	l '	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/07
4	0	438/257.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/07
5	0	438/257.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/07
6	0	438/257.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (spacer\$2) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/07
-	1	l	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/02
_	50	gate adj electrode and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (nitride adj spacers) and (channel adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/31 13:42
_	36		USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/31 14:17
_	36	1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/31 14:41
-	1	20020028541.pn. and (nitride adj layer) and (oxide adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/31 14:36
-	1	20020028541.pn. and (nitride adj spacer) and (oxide adj spacer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/31 14:36

-	13	gate adj electrode and (semiconductor adj substrate) and dielectric and source and drain and ((oxide adj spacers) same (nitride adj spacers)) and (channel adj region) and @ad<20020319	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 10:36
-	1	(gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 10:39
_	0	(gate adj stack) (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and (gate adj stack) and (non-volatile adj memory adj stack)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/07 09:17
-	1		USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 10:41
-	1		USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01
-	1	l	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 12:08
-	3	(gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and gate and (gate adj dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 12:27
-	1	6117719.pn. and ((anti-reflective adj coating) or (ARC))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01 12:10
_	1	coating) or (ARC))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/01
-	2	438/595,696,230,778-785.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and gate and (gate adj dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/03
_	1	438/366,367,368,369.ccls. and (gate adjelectrode) and (semiconductor adjsubstrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and gate and (gate adj dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/07 09:14
-	1		USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/03 10:37

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-	2	5902125.pn.	USPAT;	2004/09/01
			US-PGPUB;	14:40
			EPO; JPO;	i
	ا	5960270.pn.	DERWENT USPAT;	2004/09/01
-		5960270.pn.	US-PGPUB;	14:43
			EPO; JPO;	11.13
			DERWENT	
_	2	5972762.pn.	USPAT;	2004/09/01
	Į	-	US-PGPUB;	14:44
			EPO; JPO;	
	ĺ		DERWENT	
-	0	6066567pn.	USPAT;	2004/09/01
			US-PGPUB;	14:44
			EPO; JPO;	
	2	6066567.pn.	DERWENT USPAT;	2004/09/01
-		6066367.pn.	US-PGPUB;	14:45
			EPO; JPO;	
			DERWENT	
_	2	6087271.pn.	USPAT;	2004/09/01
		- -	US-PGPUB;	14:50
	ļ		EPO; JPO;	
İ			DERWENT	
-	2	6156126.pn.	USPAT;	2004/09/01
	1		US-PGPUB;	14:50
			EPO; JPO;	
	2	6245682 pp	DERWENT USPAT;	2004/09/01
_	2	6245682.pn.	US-PGPUB;	14:51
			EPO; JPO;	14.01
			DERWENT	
_	2	6368947.pn.	USPAT;	2004/09/01
	_		US-PGPUB;	14:51
1			EPO; JPO;	
			DERWENT	
-	0		USPAT;	2004/09/03
		adj substrate) and dielectric and source	US-PGPUB;	09:49
		and drain and (dielectric adj spacers)	EPO; JPO; DERWENT	
		and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC)	DERWENT	
		and (anti-reflective adj coating of ARC) and (gate adj stack) and (non-volatile		
		and (gate ad) stack) and (non-volatile ad) adj memory adj stack)		
_	2		USPAT;	2004/09/01
1		(gate adj stack) and (non-volatile adj	US-PGPUB;	15:23
		memory adj stack)	EPO; JPO;	
			DERWENT	
-	. 2	6753242.pn.	USPAT;	2004/09/01
			US-PGPUB;	15:23
			EPO; JPO;	
1_	2	6066567.pn.	DERWENT USPAT;	2004/09/02
1 -		0000007.pii.	US-PGPUB;	15:34
			EPO; JPO;	
			DERWENT	
-	2	5902125.pn.	USPAT;	2004/09/02
1			US-PGPUB;	15:36
			EPO; JPO;	
			DERWENT	0004/00/00
] -	. 3	597262.pn.	USPAT;	2004/09/02
	1		US-PGPUB;	15:37
1	1		EPO; JPO; DERWENT	
_	2	6087271.pn.	USPAT;	2004/09/02
		000,2,1,pii.	US-PGPUB;	15:55
		·	EPO; JPO;	
			DERWENT	
-	2	6555397.pn.	USPAT;	2004/09/02
			US-PGPUB;	15:57
1	1		EPO; JPO;	
	<u> </u>	<u> </u>	DERWENT	

- 1 20000814.pn. USPAT; US-PGPUB; EPO; JPO; DERWENT					
- 0 20000814.pn. EPO; JPO; DERWENT USPAR; US-PGPUB; EPO; JPO; DERWENT USPAR; USPAR; US-PGPUB; EPO; JPO; DERWENT USPAR; US-PGPUB; EPO; JPO; DERWENT USPAR; US-PGPUB; EPO; JPO; DERWENT USPAR;	-	1	20000816.pn.	USPAT;	2004/09/02
-				·	16:00
- 2 6136636.pn. USPAT;				EPO; JPO;	
16:35 16:3				DERWENT	
Process Proc	-	0	20000814.pn.	USPAT;	, ,
2 6136636.pn.				US-PGPUB;	16:35
2 6136636.pn. USPAT; US-PGPUB; EPC; JPC; DERWENT USPAT; US-PGPUB; EPC; JPC; DERWENT USPAT; USP			· ·	EPO; JPO;	
Second				DERWENT	
- 2 6177743.pn.	_	2	6136636.pn.	USPAT;	2004/09/03
2			-	US-PGPUB;	09:34
2 6177743.pn. USPAT; USP		,		EPO; JPO;	
Section Sect				DERWENT	
September Sept	_	2	61177743.pn.	USPAT;	2004/09/02
2 6372589.pn. DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO;			-	US-PGPUB;	16:57
Comparison			,	EPO; JPO;	
US-PGPUB; EPO, JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT;				DERWENT	
17:24 17:24 17:24 17:24 17:24 17:24 17:25 17:2	_	2	6372589.pn.	USPAT;	2004/09/02
DERWENT USPAT: U		_	.	US-PGPUB;	17:24
DERWENT USPAT: U	}			EPO; JPO;	
- 2 6368947.pn. USPAT; US-PGPUB; EPO; JPO; DREWENT					
17:25 17:26 17:26 17:26 17:26 17:26 17:27 17:27 17:27 17:27 17:27 17:27 17:27 17:28 17:27 17:28 17:2	_	2	6368947.pn.		2004/09/02
- 2 6245682.pm.				,	
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2 6245682.pn. USPAT; USPAT; USPAT; POWN DERWENT USPAT; USP				•	
US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EFO; JPO; JPO; DERWENT USPAT; US-PGPUB; EFO; JPO; JPO; DERW	I _	2	6245682.pn.		2004/09/02
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EPO; JPO; DERWENT USPAT; 2004/09/02 US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO;	-		0130120.pm.	· ·	1
- 2 6097271.pn. DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO	1				1 17.20
- 2 6087271.pn. USPAT; US-PGPUB; EPC; JPC; DERWENT					!
US-PGPUB EPO; JPO; DERWENT USPAT; US-PGPUB EPO; JPO; JPO; DERWENT USPAT; US-PGPUB EPO; JPO; JPO; DERWENT USPAT; US-PGPUB EPO; JPO;			(007271 mm		2004/09/02
- 2 6087271.pn. EPO: JPO: DERWENT USPAT; US-PGPUB; USPAT; USPAT; US-PGPUB; USPAT; US-PG	-		6097271.pm.	· ·	
- 2 6087271.pn. - 2 6086567.pn. - 2 6066567.pn. - 2 6066567.pn. - 2 5972762.pn. - 2 5972762.pn. - 2 5960270.pn. - 2 5960270.pn. - 2 5960270.pn. - 2 5902125.pn. - 3 5902125.pn. - 438/595,696,230,778-785.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) - 1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) - 1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) - 1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) - 1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) - 2 6066567.pn. - 2 5972762.pn. - 2 5960270.pn. - 2 6004/09/02 - 17:34 - 2004/09/02 - 17:36 - 2004/09/02 - 17:36 - 2004/09					17.27
- 2 6087271.pn. USPAT; US-PGPUB; EPO; JPO; DERWENT				1	
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- 2 5972762.pn. DERWENT USPAT; 2004/09/02 17:28 - 2 5960270.pn. USPAT;					17:28
- 2 5972762.pn. USPAT; US-PGPUB; EPO; JPO; DERWENT US-PGPU	İ				
US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT US		_	5070760		3004/00/03
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- 2 438/595,696,230,778-785.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) 1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) 2004/09/02 17:34 2004/09/02 17:34 2004/09/02 17:34				1	
adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) 1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and 17:34 17:34 17:34 17:34 17:34 17:34 17:34 17:34 17:34 17:34 17:34		1	,		
substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) 1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and	-	2			
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(channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) 1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and					
(anti-reflective adj coating or ARC) 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and		I		DERWENT	
1 438/366,367,368,369.ccls. and (gate adj electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and					
electrode) and (semiconductor adj substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and]
substrate) and dielectric and source and drain and (oxide adj spacers) and (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and	-	1			1 ' '
drain and (oxide adj spacers) and DERWENT (channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and					17:34
(channel adj region) and @ad<20020319 and (anti-reflective adj coating or ARC) and		[
(anti-reflective adj coating or ARC) and				DERWENT	
gate			(anti-reflective adj coating or ARC) and		
			gate		

	0	6136636.pn. and non-volatile	USPAT;	2004/09/03
_	0	6138836.pm. and non-volatile	US-PGPUB;	09:36
]	l		EPO; JPO;	09.30
!			DERWENT	
		6136636 nn and moments	USPAT;	2004/09/03
-	"	6136636.pn. and memory	US-PGPUB;	09:38
			EPO; JPO;	09.50
			DERWENT	
	0	6136636.pn. and floating	USPAT;	2004/09/03
-	"	6136636.pii. and 110acing	US-PGPUB;	09:38
			EPO; JPO;	09.30
			DERWENT	
		And concerns and forth moffernies and	USPAT;	2004/09/03
-	0	@ad<20020319 and (anti-reflective adj	US-PGPUB;	09:50
		coating or ARC) and (gate adj stack) and	1	09:50
		(non-volatile adj memory adj stack)	EPO; JPO;	
			DERWENT	0004/00/03
-	Ó		USPAT;	2004/09/03
		coating or ARC) and ((gate adj stack) or	US-PGPUB;	09:53
		(transistor)) and (non-volatile adj	EPO; JPO;	
1	· .	memory adj stack)	DERWENT	2004/00/02
-	0	@ad<20020319 and ((anti-reflective adj	USPAT;	2004/09/03
		coating) or (ARC or BARC)) and ((gate adj	US-PGPUB;	09:55
		stack) or (transistor)) and (non-volatile	EPO; JPO;	
		adj memory adj stack)	DERWENT	2004/00/03
-	350	@ad<20020319 and ((anti-reflective adj	USPAT;	2004/09/03
		coating) or (ARC or BARC)) and ((gate adj	US-PGPUB;	09:56
		stack) or (transistor)) and (non-volatile	EPO; JPO;	1
		adj memory)	DERWENT	2004/00/02
_	48	@ad<20020319 and ((anti-reflective adj	USPAT;	2004/09/03
		coating) or (ARC)) and ((gate adj stack)	US-PGPUB;	10:02
		or (gate adj transistor)) and	EPO; JPO;	
ļ		(non-volatile adj memory)	DERWENT	0004/00/00
-	13	·	USPAT;	2004/09/03
		coating) or (ARC)) and ((gate adj stack)	US-PGPUB;	10:02
		or (gate adj transistor)) and	EPO; JPO;	
		(non-volatile adj memory) and spacers	DERWENT	2004/00/06
-	1	438/366,367,368,369,303.ccls. and (gate	USPAT;	2004/09/06
	Į	adj electrode) and (semiconductor adj	US-PGPUB;	17:24
		substrate) and dielectric and source and	EPO; JPO;	
ļ		drain and (oxide adj spacers) and	DERWENT	
		(channel adj region) and @ad<20020319 and		
1	_	(anti-reflective adj coating or ARC)	HCDAM -	2004/00/00
-	2		USPAT;	2004/09/06
		adj electrode) and (semiconductor adj	US-PGPUB;	17:24
ŀ		substrate) and dielectric and source and	EPO; JPO;	
		drain and (oxide adj spacers) and	DERWENT	
		(channel adj region) and @ad<20020319 and		
		(anti-reflective adj coating or ARC)	IIGDAE :	2004/00/07
-	19		USPAT;	2004/09/07
		adj electrode) and (semiconductor adj	US-PGPUB;	09:10
		substrate) and dielectric and source and	EPO; JPO;	
		drain and (oxide adj spacers) and	DERWENT	
		(channel adj region)	IIGDAE :	2004/00/06
-	22	438/595,696,230,778-785.ccls. and (gate	USPAT;	2004/09/06
		adj electrode) and (semiconductor adj	US-PGPUB;	17:24
		substrate) and dielectric and source and	EPO; JPO;	
		drain and (oxide adj spacers) and	DERWENT	
1		(channel adj region)		